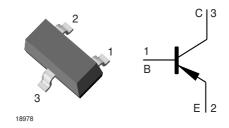


Vishay Semiconductors

Small Signal Transistor (PNP)

Features

- PNP Silicon Epitaxial Planar Transistors for switching and AF amplifier applications.
- Suited for low level, low noise, low frequency applications in hybrid circuits.
- · Low current, low voltage.
- As complementary types, BCX70 Series NPN transistors are recommended.



Mechanical Data

Case: SOT-23 Plastic case

Weight: approx. 8.8 mg

Marking: BCX71G = BG BCX71H = BH BCX71J = BJ BCX71K = BK

Packaging Codes/Options:

GS18 / 10 k per 13" reel (8 mm tape), 10 k/box GS08 / 3 k per 7" reel (8 mm tape), 15 k/box

Pinning:

1 = Base, 2 = Emitter, 3 = Collector

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Collector - base voltage		- V _{CBO}	45	V
Collector - emitter voltage		- V _{CEO}	45	V
Emitter - base voltage		- V _{EBO}	5.0	V
Collector current		- I _C	200	mA
Peak base current		- I _B	50	mA
Power dissipation		P _{tot}	250	mW

Maximum Thermal Resistance

Parameter	Test condition	Symbol	Value	Unit	
Thermal resistance junction to ambient air		$R_{ hetaJA}$	500 ¹⁾	°C/W	
Junction temperature		T _j	150	°C	
Storage temperature range		T _S	- 65 to + 150	°C	

¹⁾ Mounted on FR-4 printed-circuit board.

BCX71 Series

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Electrical DC Characteristics

Parameter	Test condition	Part	Symbol	Min	Тур	Max	Unit
DC current gain	$- V_{CE} = 5 V, - I_{C} = 10 \mu A$	BCX71G	h _{FE}				
		BCX71H	h _{FE}	30			
		BCX71J	h _{FE}	40			
		BCX71K	h _{FE}	100			
	- V _{CE} = 5 V, - I _C = 2 mA	BCX71G	h _{FE}	120		220	
		BCX71H	h _{FE}	180		310	
		BCX71J	h _{FE}	250		460	
		BCX71K	h _{FE}	380		630	
	- V _{CE} = 1 V, - I _C = 50 mA	BCX71G	h _{FE}	60			
		BCX71H	h _{FE}	80			
		BCX71J	h _{FE}	100			
		BCX71K	h _{FE}	110			
Collector - emitter saturation voltage	- I _C = 10 mA, - I _B = 0.25 mA		- V _{CEsat}	60		250	mV
	- I _C = 50 mA, - I _B = 1.25 mA		- V _{CEsat}	120		550	mV
Base - emitter saturation voltage	- I _C = 10 mA, - I _B = 0.25 mA		- V _{BEsat}	600		850	mV
	- I _C = 50 mA, - I _B = 1.25 mA		- V _{BEsat}	680		1050	mV
Base - emitter voltage	- V _{CE} = 5 V, - I _C = 2 mA		- V _{BE}	600	650	750	mV
	$- V_{CE} = 5 V, - I_{C} = 10 \mu A$		- V _{BE}		520		mV
	- V _{CE} = 5 V, - I _C = 50 mA		- V _{BE}		780		mV
Collector cut - off current	- V _{CB} = 45 V, V _{EB} = 0 V		- I _{CBO}			20	nA
	- V _{CB} = 45 V, V _{EB} = 0 V, T _A = 150 °C		- I _{CBO}			20	μΑ
Emitter cut - off current	- V _{EB} = 4 V, I _C = 0		- I _{EBO}			20	nA

Electrical AC Characteristics

Parameter	Test condition	Part	Symbol	Min	Тур	Max	Unit
Gain - bandwidth product	$- V_{CE} = 5 V, - I_{C} = 10 mA,$ f = 100 MHz		f _T	100			MHz
Collector - base capacitance	- V _{CB} = 10 V, f = 1 MHz, I _E = 0		C _{CBO}		4.5		pF
Emitter - base capacitance	$- V_{CB} = 0.5 \text{ V, f} = 1 \text{ MHz, I}_{E} = 0$		C _{EBO}		11		pF
Noise figure	- V_{CE} = 5 V, - I_{C} = 200 μ A, R_{S} = 2 k Ω , f = 100 kHz, B = 200 Hz		F		2	6	dB
Small signall current gain	$-V_{CE} = 5 \text{ V}, -I_{C} = 2 \text{ mA}, f = 1 \text{ kHz}$	BCX71G	h _{fe}		200		
		BCX71H	h _{fe}		260		
		BCX71J	h _{fe}		330		
		BCX71K	h _{fe}		520		
Turn - on time at R _L = 99 Ω (see fig.1)	$- V_{Cc} = 10 \text{ V}, - I_{C} = 10 \text{ mA},$ $I_{B(on)} = - I_{B(off)} = 1 \text{ mA}$		t _{on}		85	150	ns
Turn - off time at R _L = 99 Ω (see fig.1)	$-V_{Cc} = 10 \text{ V}, -I_{C} = 10 \text{ mA},$ $I_{B(on)} = -I_{B(off)} = 1 \text{ mA}$		t _{off}		480	800	ns



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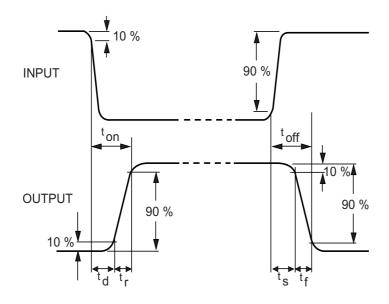
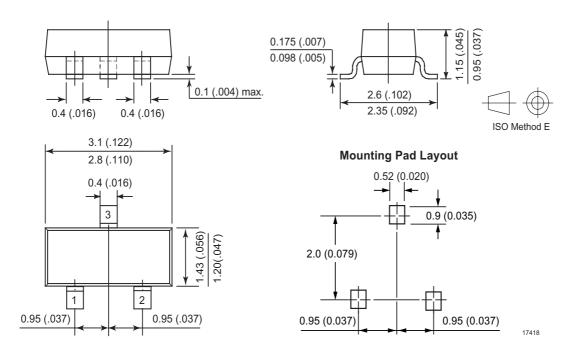


Figure 1. Switching Waveform

Package Dimensions in mm (Inches)



Document Number 85139 Rev. 1.2, 19-Aug-04

BCX71 Series

Vishay Semiconductors



Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

- 1. Meet all present and future national and international statutory requirements.
- 2. Regularly and continuously improve the performance of our products, processes, distribution and operatingsystems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

- 1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
- 2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
- 3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Semiconductors products for any unintended or unauthorized application, the buyer shall indemnify Vishay Semiconductors against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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Document Number 85139

Rev. 1.2, 19-Aug-04

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